

# 4V Drive Nch+Nch MOSFET

# SH8K22

#### Structure

Silicon N-channel MOSFET

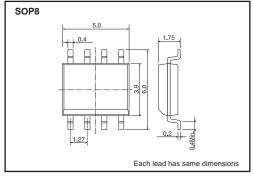
### Features

Built-in G-S Protection Diode.
Small surface Mount Package (SOP8).

#### Application

Power switching, DC / DC converter, Inverter

# •Dimensions (Unit : mm)



### Packaging specifications

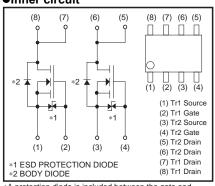
	Package	Taping
Туре	Code	ТВ
	Basic ordering unit (pieces)	2500
SH8K22		0

# •Absolute maximum ratings (Ta=25°C)

< It is the same ratings for the Tr1 and Tr2.>

Paramete	r	Symbol	Limits	Unit	
Drain-source voltage		V <sub>DSS</sub>	45	V	
Gate-source voltage		V <sub>GSS</sub>	±20	V	
Drain current	Continuous	Ι <sub>D</sub>	±4.5	A	
	Pulsed	I <sub>DP ∗1</sub>	±18	А	
Source current	Continuous	I <sub>S</sub>	1	A	
(Body diode)	Pulsed	I <sub>SP ∗1</sub>	18	A	
Total power dissipation		P <sub>D ∗2</sub>	2	W / TOTAL	
			1.4	W / ELEMENT	
Chanel temperature		T <sub>ch</sub>	150	°C	
Range of Storage temperature		T <sub>stg</sub>	-55 to +150	°C	





A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use. Use the protection circuit when the fixed voltages are exceeded.

\*1 PW  $\leq$  10 $\mu$ s, Duty cycle  $\leq$  1%

\*2 Mounted on a ceramic board

#### •Electrical characteristics (Ta=25°C) <It is the same characteristics for the Tr1 and Tr2.>

<u><it characterist<="" is="" same="" the="" u=""> Parameter</it></u>	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	_	_	±10	μA	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V
Drain-source breakdown voltage	V(BR) DSS	45	_	-	V	I <sub>D</sub> = 1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	IDSS	_	_	1	μA	Vps= 45V, Vgs=0V
Gate threshold voltage	VGS (th)	1.0	-	2.5	V	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA
Static drain-source on-state resistance	$R_{DS}(on)^*$	-	33	46	mΩ	I <sub>D</sub> = 4.5A, V <sub>GS</sub> = 10V
		-	41	57	mΩ	I <sub>D</sub> = 4.5A, V <sub>GS</sub> = 4.5V
		-	46	64	mΩ	ID= 4.5A, VGS= 4.0V
Forward transfer admittance	Y <sub>fs</sub> *	3.5	_	-	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 4.5A
Input capacitance	Ciss	-	550	-	pF	V <sub>DS</sub> = 10V
Output capacitance	Coss	-	140	_	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	Crss	-	70	_	pF	f=1MHz
Turn-on delay time	t <sub>d (on)</sub> *	-	12	_	ns	Vdd≒25V
Rise time	tr *	-	18	_	ns	$I_{D}= 2.5A$
Turn-off delay time	td (off) *	-	42	-	ns	Vgs= 10V R∟= 10Ω
Fall time	tr *	-	12	_	ns	Rg=10Ω
Total gate charge	Qg *	-	6.8	9.6	nC	V <sub>DD</sub> ≒25V, V <sub>GS</sub> =5V
Gate-source charge	Q <sub>gs</sub> *	-	2.0	-	nC	I <sub>D</sub> = 4.5A
Gate-drain charge	Q <sub>gd</sub> *	_	2.9	-	nC	R <sub>L</sub> = 5.6Ω, R <sub>G</sub> = 10Ω

\*Pulsed

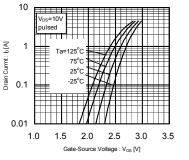
# •Body diode characteristics (Source-Drain) (Ta=25°C)

< It is the same characteristics for the Tr1 and Tr2.>

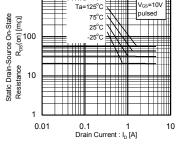
	Symbol	Min.	l yp.	Max.	Unit	Condition
Forward voltage	V <sub>SD</sub> *	_	_	1.2	V	I <sub>S</sub> =4.5A/V <sub>GS</sub> =0V

\* pulsed

### •Electrical characteristic curves







1000

Fig.2 Static Drain-Source On-State Resistance vs. Drain Current (1)

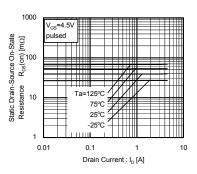


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current (2)

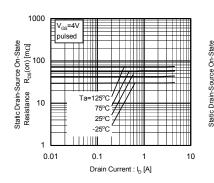


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current (3)

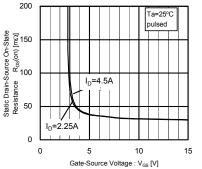


Fig.5 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

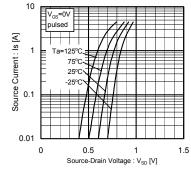


Fig.6 Source-Current vs. Source-Drain Voltage

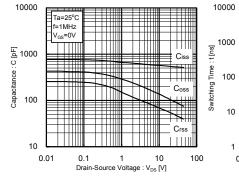


Fig.7 Typical capacitance vs. Source-Drain Voltage

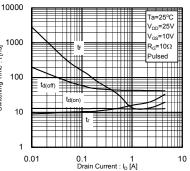


Fig.8 Switching Characteristics

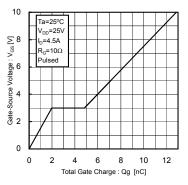


Fig.9 Dynamic Input Characteristics

# Measurement circuits

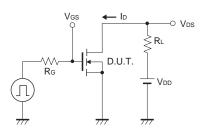


Fig.10 Switching Time Test Circuit

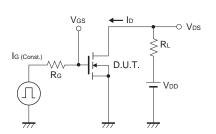


Fig.12 Gate Charge Test Circuit

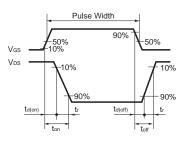


Fig.11 Switching Time Waveforms

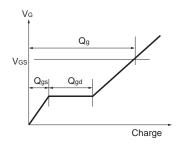


Fig.13 Gate Charge Waveform

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